

Supporting Information for

Designing a family of 2D kagome monolayer $B_{18}S_8$, $B_{18}S_8H_2$, $B_{18}S_6X_2$ ($X=Cl, Br, I$) with tunable Dirac cones and high Fermi velocity

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Note 1. Details for computational method.

The calculations employed the projector augmented-wave (PAW) method[1,2], seamlessly integrated within the VASP code[3,4]. The valence electron configurations were specified as follows: 1s for H, 2s and 2p for B, 3s and 3p for S, 3s and 3p for Cl, 4s and 4p for Br, 5s and 5p for I. A plane wave cutoff energy of 500 eV was established for these configurations. For the determination of the exchange-correlation energy, the generalized gradient approximation (GGA) within the Perdew-Burke-Ernzerhof (PBE) scheme was adopted[5]. During the structural optimization phase, stringent criteria were imposed, including a force criterion of 0.001 eV/Å in any direction, an energy criterion of 10^{-7} eV, and the utilization of a dense $11 \times 11 \times 1$ Γ -centered k -mesh. Furthermore, to avoid the interactions between adjacent layers,[6–8] the a vacuum slab of up to 20 Å was introduced for all 2D structures along the z-direction. Additionally, phonon dispersion, grounded in density functional perturbation theory (DFPT), was computed using *Phonopy*[9] software. The VASPKIT code[10] served as a valuable tool in facilitating the data analysis process.

Note 2. Calculated method for Young's modulus Y and Poisson's ratio ν .

For the angle dependent in-plane Young's modulus (Y) and Poisson's ratio (ν) are calculated using the independent elastic constants (C_{11} , C_{22} , C_{12} and C_{66}). The calculation formula is as follows:[11]

$$Y(\theta) = \frac{C_{11}C_{22} - C_{12}^2}{C_{11}\sin^4\theta + C_{22}\cos^4\theta + \left(\frac{C_{11}C_{22} - C_{12}^2}{C_{66}} - 2C_{12}\right)\cos^2\theta\sin^2\theta}$$
$$\nu(\theta) = \frac{C_{12}(\sin^4\theta + \cos^4\theta) - (C_{11} + C_{22} - \frac{C_{11}C_{22} - C_{12}^2}{C_{66}})\cos^2\theta\sin^2\theta}{C_{11}\sin^4\theta + C_{22}\cos^4\theta + \left(\frac{C_{11}C_{22} - C_{12}^2}{C_{66}} - 2C_{12}\right)\cos^2\theta\sin^2\theta}$$

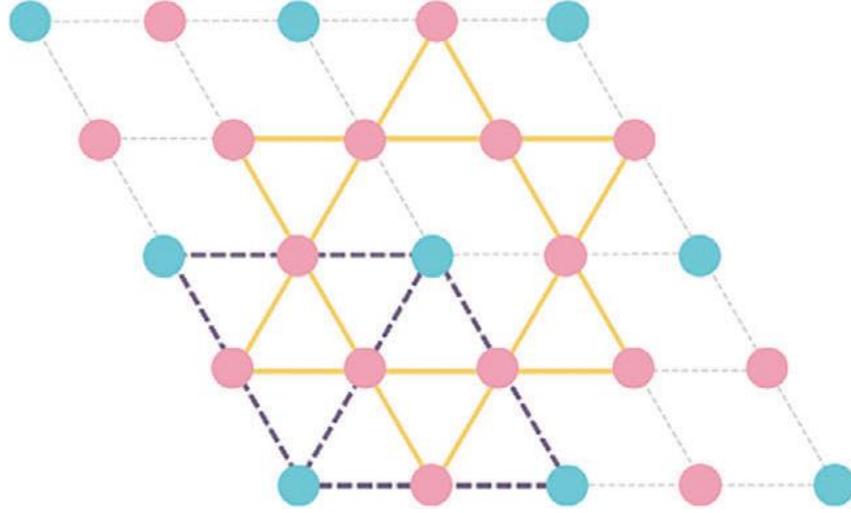


Fig. S1. Schematic diagram of constructing a kagome lattice from a triangular lattice based on the "1+3" strategy.

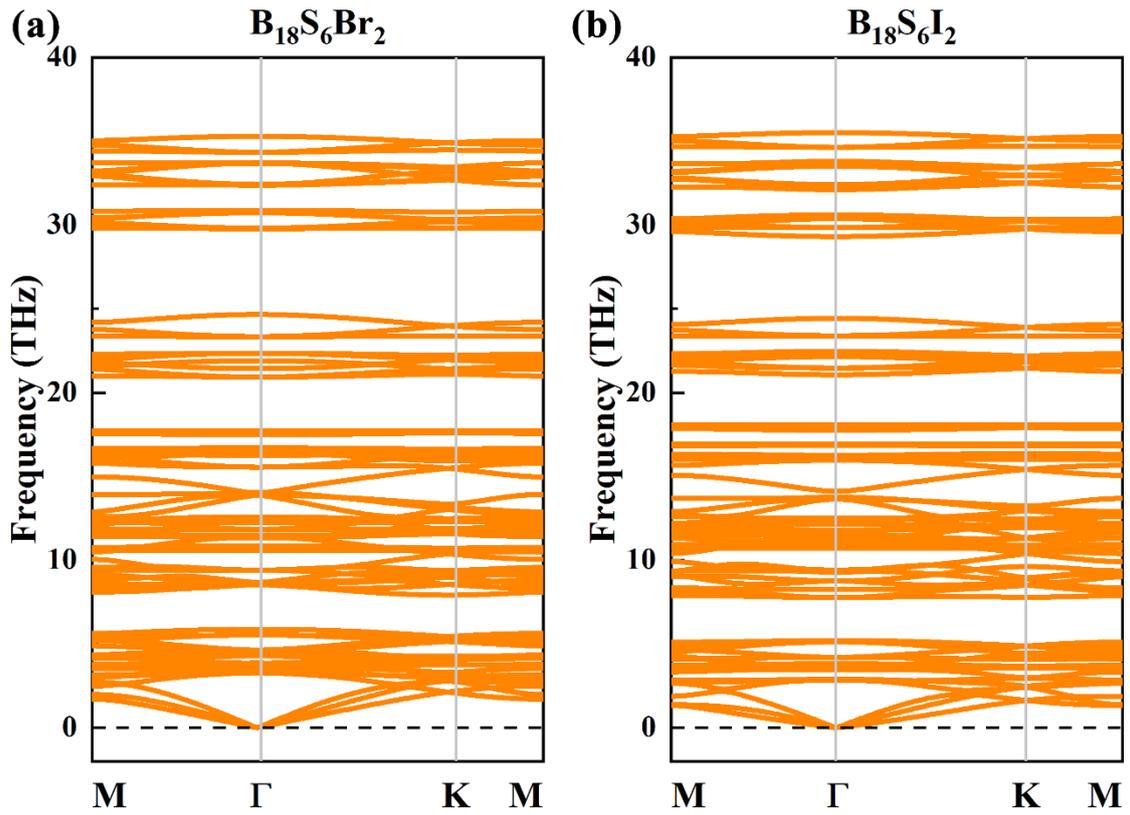


Fig. S2. Phonon dispersions of states of (a) $B_{18}S_6Br_2$ and (b) $B_{18}S_6I_2$ monolayers.

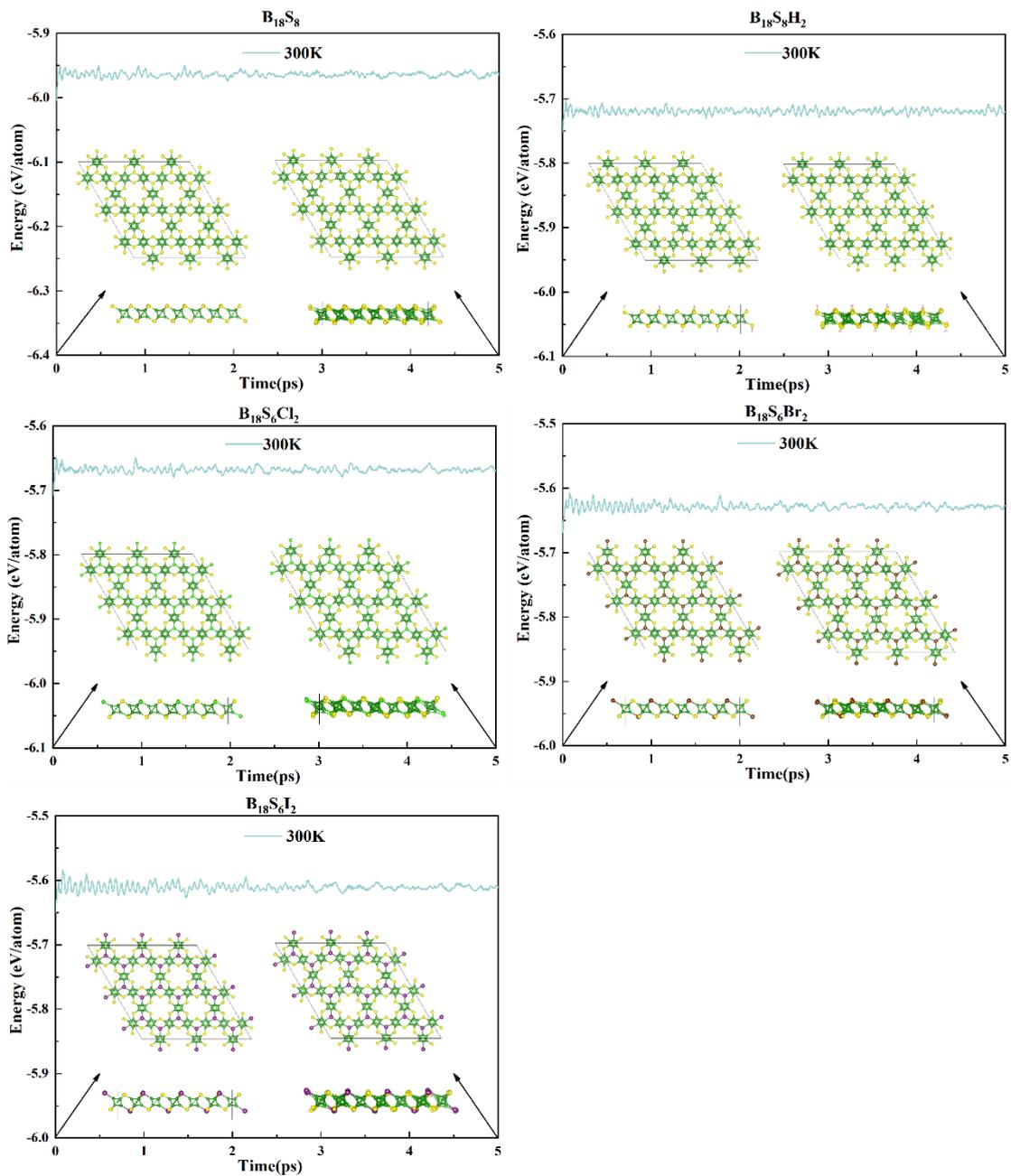


Fig. S3. AIMD simulations of $B_{18}S_8$, $B_{18}S_8H_2$, $B_{18}S_6X_2$ ($X = Cl, Br, I$) monolayers at 300 K.

Table S1. Calculated independent elastic constants C_{ij} of $B_{18}S_8$, $B_{18}S_8H_2$, $B_{18}S_6X_2$ ($X = Cl, Br, I$) monolayers.

Materials	C_{11}/C_{22}	C_{12}	C_{66}	$C_{11}C_{22} - C_{12}^2 > 0$
$B_{18}S_6$	118.46	28.45	45.01	True
$B_{18}S_8$	66.52	20.30	23.11	True
$B_{18}S_8H_2$	72.76/72.81	25.12	23.83	True
$B_{18}S_6Cl_2$	59.40	16.62	21.39	True
$B_{18}S_6Br_2$	54.57	15.34	19.62	True
$B_{18}S_6I_2$	51.92	14.54	18.71	True

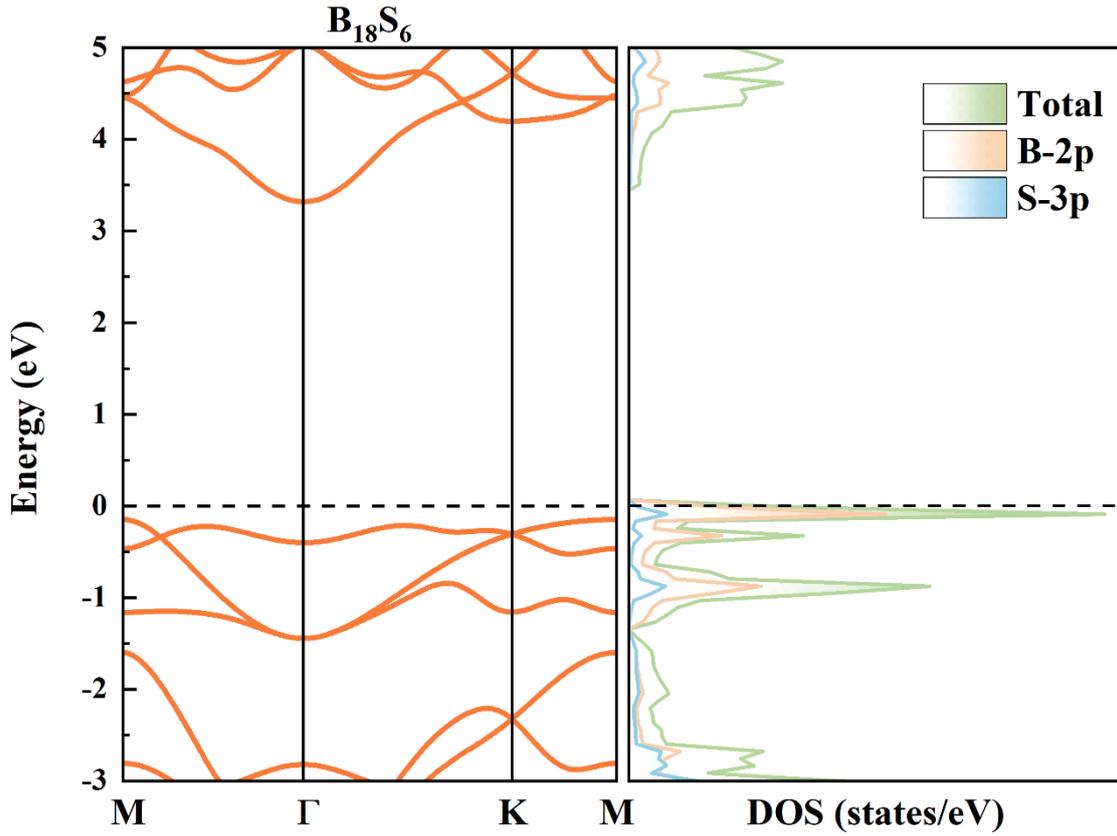


Fig. S4. Band structure and density of states of $B_{18}S_6$ monolayer using the primitive cell based on GGA-PBE calculations.

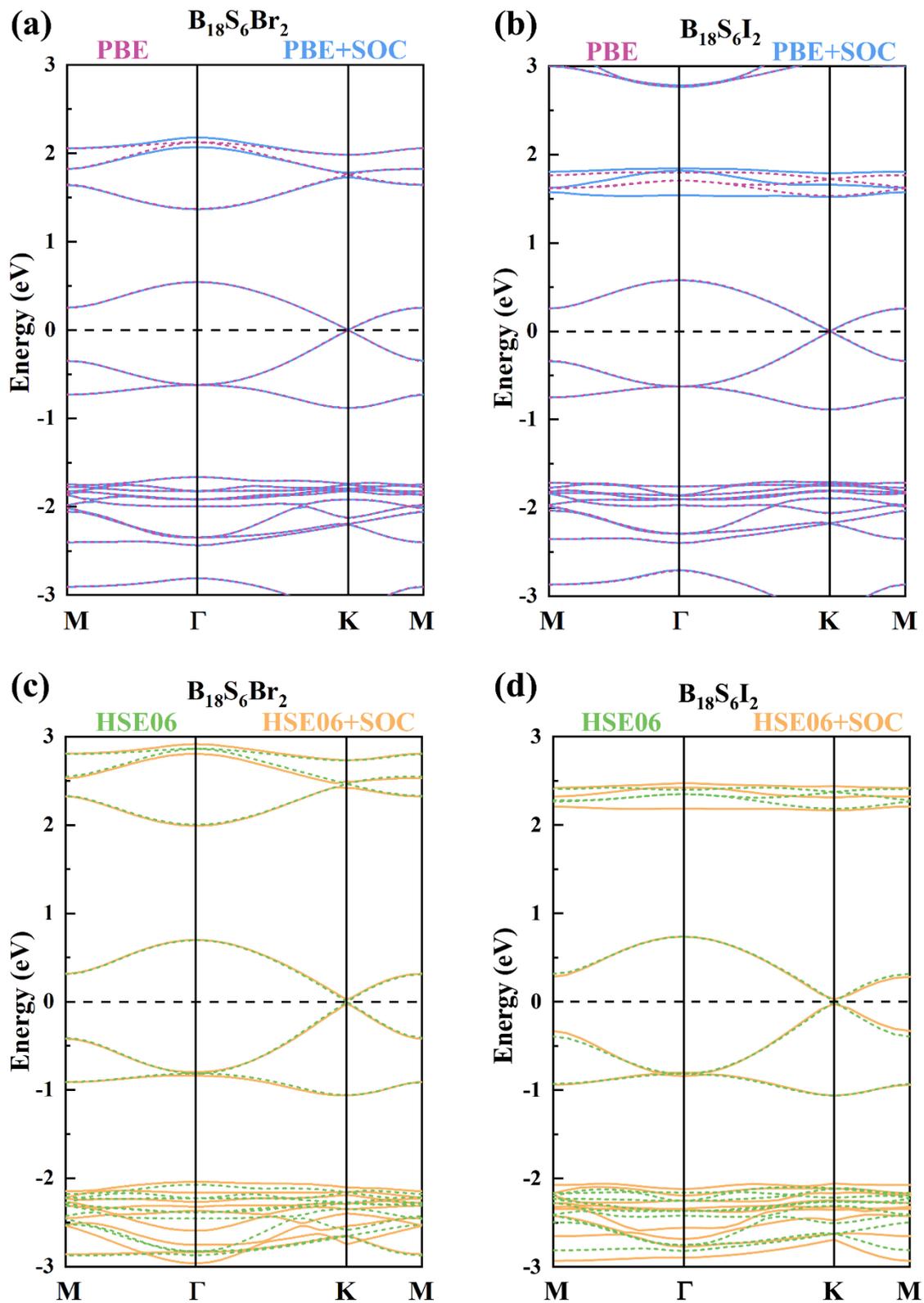


Fig. S5. Band structure of $B_{18}S_6Br_2$ and $B_{18}S_6I_2$ monolayer based on GGA-PBE and HSE06 calculations with/without SOC effect considered.

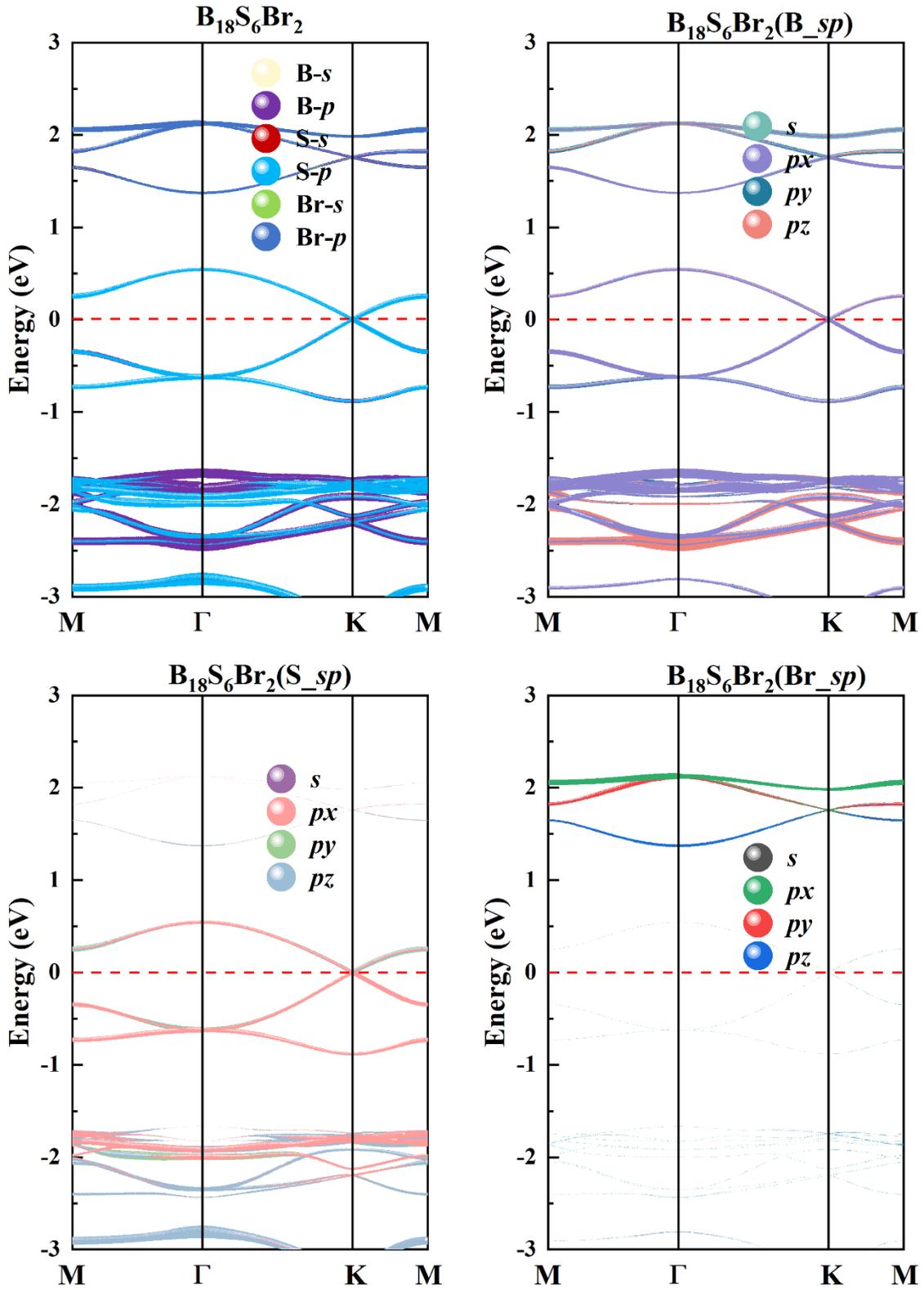


Fig. S6. Projected band structures of $B_{18}S_6Br_2$ monolayer based on GGA-PBE calculations.

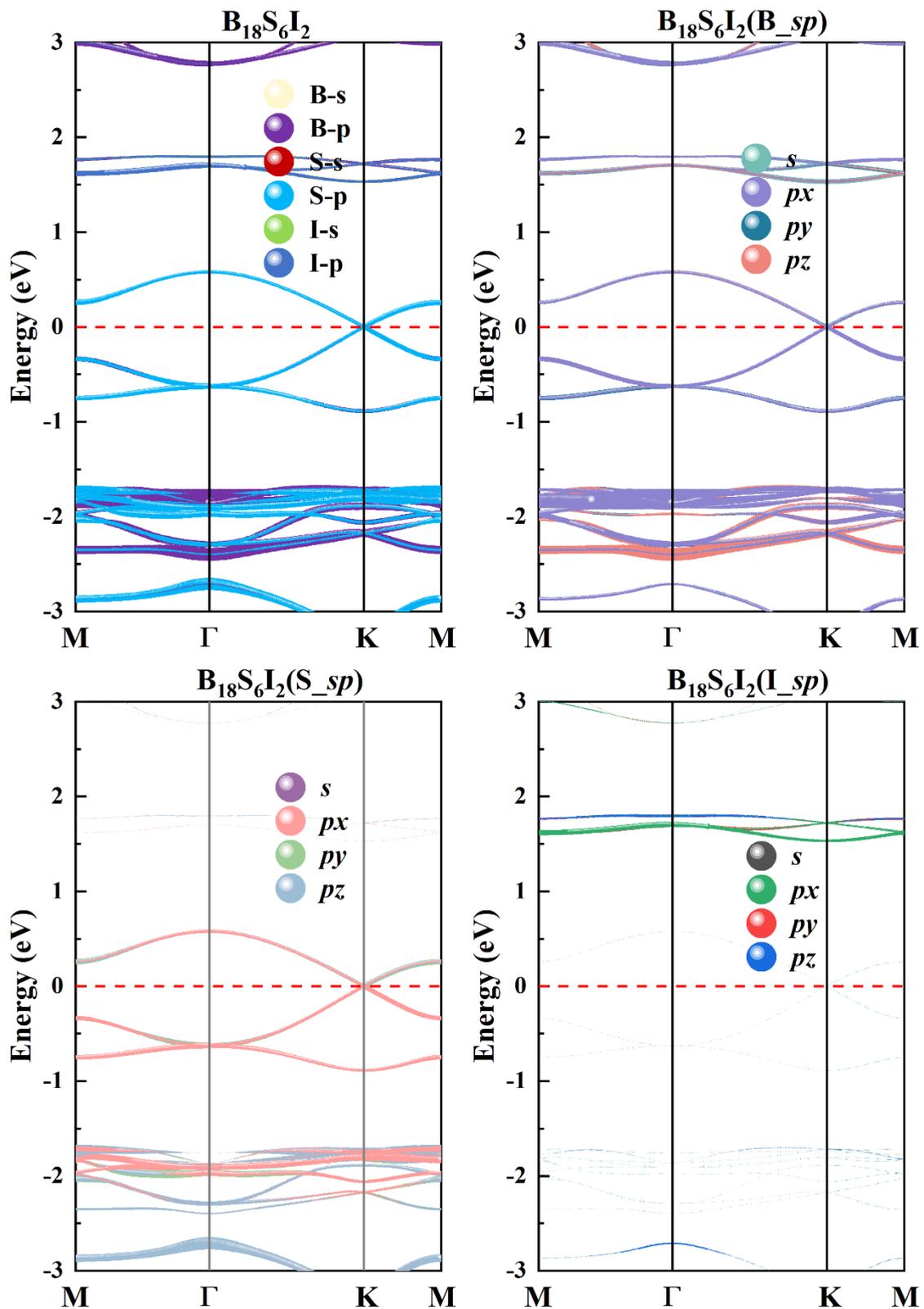


Fig. S7. Projected band structures of $B_{18}S_6I_2$ monolayer based on GGA-PBE calculations.

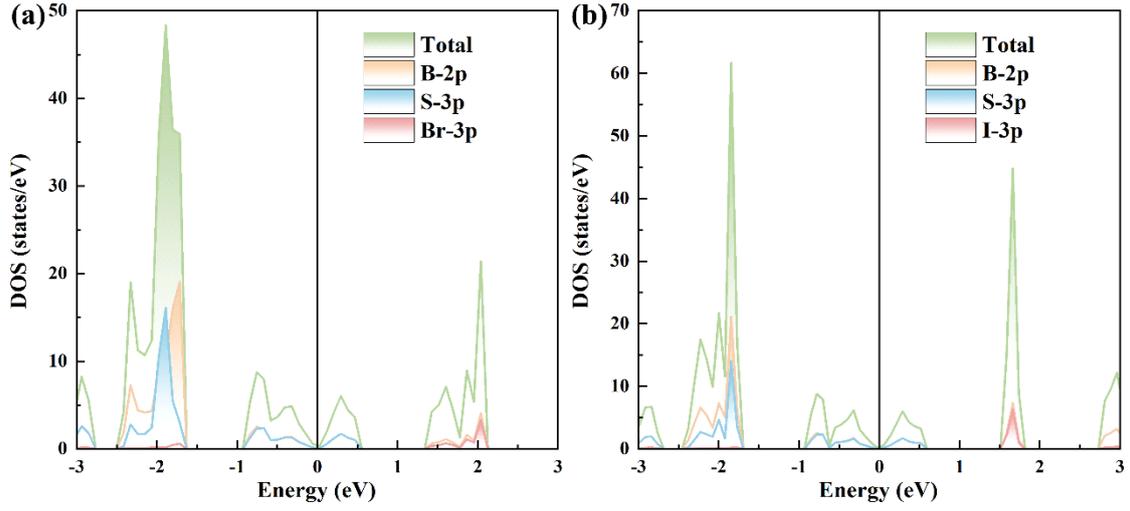


Fig. S8. Density of states of (a) $B_{18}S_6Br_2$ and $B_{18}S_6I_2$ monolayers based on GGA-PBE calculations.

Table S2. Calculated Fermi velocity at the Dirac cone of $B_{18}S_8$, $B_{18}S_8H_2$ and $B_{18}S_6X_2$ ($X = Cl, Br, I$) monolayers along Γ -K and K-M direction.

Materials	V_F^{G-K}	V_F^{K-M}
$B_{18}S_8$	2.716×10^5 m/s	2.690×10^5 m/s
$B_{18}S_8H_2$	2.947×10^5 m/s	2.930×10^5 m/s
$B_{18}S_6Cl_2$	2.873×10^5 m/s	2.840×10^5 m/s
$B_{18}S_6Br_2$	2.961×10^5 m/s	2.941×10^5 m/s
$B_{18}S_6I_2$	3.067×10^5 m/s	3.046×10^5 m/s

Table S3. Calculated Fermi velocities for some 2D Dirac semimetals.

Materials	V_F (10^5 m/s)	References
graphene	8.22	[12]
g-SiC ₆	7.11	[13]
g-SiC ₃	6.0	[14]
CIPC ₆	6.31	[15]
CIPC ₃	5.11	[16]
HPC ₆	7.5	[17]

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